ON Semiconductor

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FSA642 Low-Power, Three-Port, High-Speed MIPI Switch

Features

Low On Capacitance: 7.0 pF Typical
 Low On Resistance: 7.0 Ω Typical

■ Wide -3db Bandwidth: 1 GHz Typical

■ 24-Lead UMLP (2.5 x 3.4 mm) Package

8 kV ESD Rating; >16 kV Pow er/GND ESD Rating

Applications

- Dual Camera Applications for Cell Phones
- Dual LCD Applications for Cell Phones,
 Digital Camera Displays, and View finders

Description

The FSA642 is a bi-directional, low-power, high-speed analog switch. The pin out is designed to ease differential signal layout and is configured as a triple-pole, double-throw switch (TPDT). The FSA642 is optimized for switching between two MIPI devices, such as cameras or LCD displays and on-board Multimedia Application Processors (MAP).

The FSA642 is compatible with the requirements of Mobile Industry Processor Interface (MIPI). The low-capacitance design allows the FSA642 to switch signals that exceed 500 MHz in frequency. Superior channel-to-channel crosstalk immunity minimizes interference and allows the transmission of high-speed differential signals and single-ended signals, as described by the MIPI specification.

Ordering Information

Part Number	Top Mark	Operating Temperature Range	Package
FSA642UMX	JG	-40 to +85°C	24-Lead, Quad, Ultrathin Molded Leadless Package (UMLP), 2.5 x 3.4 mm

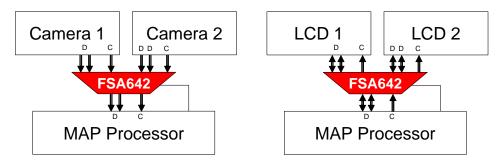


Figure 1. Application Block Diagram

Pin Configuration

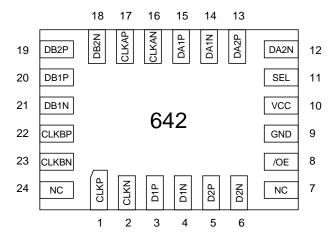


Figure 2. Pin Configuration (Top Through View)

Pin Definitions

Pin #	Name	Description
1, 2	CLKP, CLKN	Clock Path (Common)
3, 4	D1P, D1N	Data Path 1 (Common)
5, 6	D2P, D2N	Data Path 2 (Common)
7, 24	NC	No Connect (Float)
8	/OE	Output Enable (Active Low)
9	GND	Ground
10	VCC	Pow er
11	SEL	Select (0=A, 1=B)
12, 13	DA2N, DA2P	Data Path (A2)
14, 15	DA1N, DA1P	Data Path (A1)
16, 17	CLKAN, CLKAP	Clock Path (A)
18, 19	DB2N, DB2P	Data Path (2B)
20, 21	DB1P, DB1N	Data Path (1B)
22, 23	CLKBP, CLKBN,	Clock Path (B)

Functional Diagram

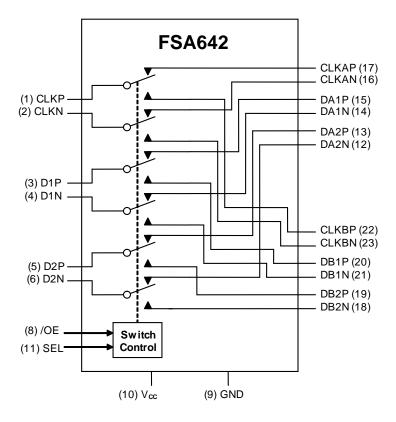


Figure 3. Functional Diagram

Truth Table

SEL	/OE	Function
Don't Care	HIGH	Disconnect
LOW	LOW	D1, D2, CLK=DA1, DA2, CLKA
HIGH	LOW	D1, D2, CLK=DB1, DB2, CLKB

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit	
Vcc	Supply Voltage		-0.50	+5.25	V
V _{CNTRL}	DC Input Voltage (SEL, /OE)(1)		-0.5	Vcc	V
V_{SW}	DC Sw itch I/O Voltage ⁽¹⁾		-0.5	V _{CC} + 0.3	V
lıĸ	DC Input Diode Current		-50		mA
lout	DC Output Current			50	mA
T _{STG}	Storage Temperature		-65	+150	°C
		All Pins		6.5	
ESD	Human Body Model, JEDEC: JESD22-A114	I/O to GND		8.0	kV
LOD	Pow er to GND			16.0	KV
	Charged Device Model, JEDEC: JESD22-C10)1		2.5	

Note:

1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
Vcc	Supply Voltage	2.65	4.30	V
V _{CNTRL}	Control Input Voltage (SEL, /OE) ⁽²⁾	0	V _{CC}	V
Vsw	Switch I/O Voltage	-0.5	V _{CC} -1	V
T _A	Operating Temperature	-40	+85	°C

Note:

2. The control input must be held HIGH or LOW; it must not float.

DC Electrical Characteristics

All typical values are T_A=25°C unless otherwise specified.

Symbol	Parameter	Conditions	V _{cc} (V)	T _A =-40 to +85°C			Units	
Joyinboi	yinsoi i arametei Conditions		▼CC (▼)	Min.	Тур.	Max.	Oilits	
Vıĸ	Clamp Diode Voltage	I _{IN} =-18 mA	2.775			-1.2	V	
l _{IN}	Control Input Leakage	V _{SW} =0 to 4.3 V	4.3	-1		1	μΑ	
VIH	Input Voltage High	V _{IN} =0 to V _{CC}	2.650 to 2.775	1.3			V	
V IH	input voltage riigh	VIN=0 to VCC		1.7			1 '	
V _{IL}	Input Voltage Low	V _{IN} =0 to V _{CC}	2.650 to 2.775			0.5	V	
loz	Off-State Leakage	A,B=0+0.3 V to V _{CC} -0.3	4.3	-2		2	μΑ	
lcc	Quiescent Supply Current	V _{CNTRL} =0 or V _{CC} , l _{OUT} =0	4.3			1.0	μΑ	
Ісст	Increase in I _{CC} Current Per Control Voltage and V _{CC}	V _{CNTRL} =1.8 V	2.775			1.5	μΑ	

DC Electrical Characteristics, Low-Speed Mode

All typical values are T_A=25°C unless otherwise specified.

Symbol Parameter		Parameter Conditions		T _A =-40 to +85°C			Units
		Conditions	V _{cc} (V)	Min.	Тур.	Max.	Omis
Ron	LS Switch On Resistance (3)	V _{SW} =1.2 V, l _{ON} =-10 mA, Figure 4	2.65		10	14	Ω
ΔR_{ON}	LS Delta R _{ON} ⁽⁴⁾	V _{SW} =1.2 V, l _{ON} =-10 mA (Intra-pair)	2.65		0.65		Ω

Notes:

- 3. Measured by the voltage drop between A/B and CLK/Dn pins at the indicated current through the switch.
- 4. Guaranteed by characterization.

DC Electrical Characteristics, High-Speed Mode

All typical values are T_A=25°C unless otherwise specified.

Symbol	Parameter Conditions		V _{cc} (V)	T _A =-40 to +85°C			Units
Cymbol	i didilicici	Oonditions	▼CC (▼)	Min.	Тур.	Max.	Office
Ron	HS Switch On Resistance (5)	V _{SW} =0.4 V, l _{ON} =-10 mA, Figure 4	2.65		7.0	9.5	Ω
ΔRon	HS Delta Ron (6)	V _{SW} =0.4 V, l _{ON} =-10 mA (Intra-pair)	2.65		0.65		Ω

Notes:

- 5. Measured by the voltage drop between A, B, and Dn pins at the indicated current through the switch.
- 6. Guaranteed by characterization.

AC Electrical Characteristics

All values are at R_L =50 Ω and R_S =50 Ω and all typical values are V_{CC} =2.775V at T_A =25 $^{\circ}$ C unless otherwise specified.

Symbol	Parameter	Conditions	V _{cc} (V)	T _A =-40°C to +85°C			Units
Symbol	raiametei	Conditions	V _{CC} (V)	Min.	Тур.	Max.	Oillis
O _{IRR}	Off Isolation ⁽⁷⁾	f=100 MHz, R_T =50 Ω Figure 14	2.775		-35		dB
Xtalk	Non-Adjacent Channel Crosstalk ⁽⁷⁾	f=100 MHz, R_T =50 Ω Figure 15	2.775		-55		dB
BW	-3 db Bandwidth ⁽⁷⁾	C_L =0 pF, R_T =50 Ω Figure 13	2.775		1.0		GHz
ton	Turn-On Time SEL, /OE to Output	C _L =5 pF, V _{SW} =1.2 V Figure 6, Figure 7	2.650 to 2.775		20	37	ns
toff	Turn-Off Time SEL, /OE to Output	C _L =5 pF, V _{SW} =1.2 V Figure 6, Figure 7	2.650 to 2.775		15	27	ns
t _{PD}	Propagation Delay ⁽⁷⁾	C _L =5 pF Figure 6, Figure 8	2.775		0.25		ns
t _{BBM}	Break-Before-Make Time	C _L =5 pF, V _{SW1} =V _{SW2} =1.2 V Figure 12	2.650 to 2.775	3	5	8	ns

Note:

AC Electrical Characteristics, High-Speed

All typical values are V_{CC} =2.775V at T_A =25°C unless otherwise specified.

Symbol	Parameter	Conditions	$T_A = -40^{\circ}C$ to $+85^{\circ}C$			Units
Syllibol	raiailletei	Conditions	Min.	Тур.	Max.	Ullits
tSK(Part_Part)	Channel-to-Channel Skew Across Multiple Parts ^(8,9)	V _{SW} =0.2 Vdiff _{PP} , C _L =5 pF		40	80	ps
tsk(chl_chl)	Channel-to-Channel Skew Within a Single Part ⁽⁸⁾	V _{SW} =0.2 Vdiff _{PP} , C _L =5 pF, Figure 9		15	30	ps
t _{SK(Pulse)}	Skew of Opposite Transitions in the Same Differential Channel (8)	V _{SW} =0.2 Vdiff _{PP} , C _L =5 pF		10	20	ps

Notes

- 8. Guaranteed by characterization.
- 9. Assumes the same V_{CC} and temperature for all devices.

Capacitance

Symbol	Parameter	Conditions	T _A =-40°C to +85°C			Units
Syllibol	Farailletei	Conditions	Min.	Тур.	Max.	Ullits
C _{IN}	Control Pin Input Capacitance ⁽¹⁰⁾	V _{CC} =0 V		1.5		
Con	Dn/CLK- On Capacitance ⁽¹⁰⁾	V _{CC} =2.775 V, /OE=0 V, f=1 MHz, at 25°C, Figure 11	6.0	7.0	9.0	pF
Coff	Dn/CLK Off Capacitance (10)	V _{CC} =2.775 V, /OE=2.775 V, f=1 MHz, Figure 10		2.5		

Note:

10. Guaranteed by characterization.

^{7.} Guaranteed by characterization.

Test Diagrams

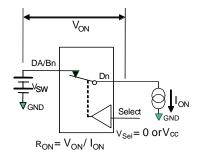
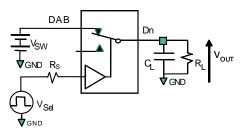


Figure 4. On Resistance



 $R_L^{}$, $R_S^{}$, an $\;C_L^{}$ are functions of the application environment (see AC Tables for spellific vilues) $C_L^{}$ inclures test fixture an $\;$ strain capacitance

Figure 6. AC Test Circuit Load

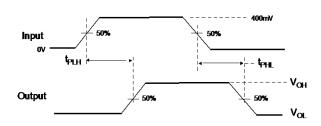


Figure 8. Propagation Delay (t_Rt_F - 500 ps)

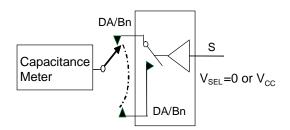
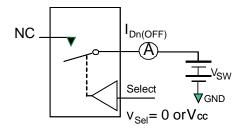


Figure 10. Channel Off Capacitance



**Each switch port is tested separately

Figure 5. Off Leakage

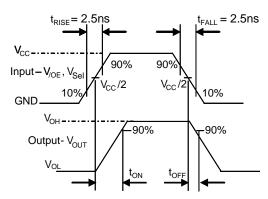


Figure 7. Turn-On / Turn-Off Waveforms

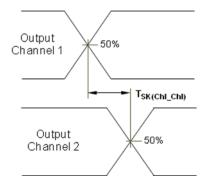


Figure 9. Channel-to-Channel Skew

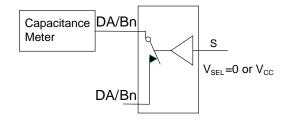


Figure 11. Channel On Capacitance

Test Diagrams (Continued) HSDn Dn Unput-V_{Sel} V_{our} V_{our} V_{our} 0.9*V_o t

 R_L , R_S , and C_L ar functions of the application environment (see AC Tables for specific v Iues). C_L includes test fixture and stra capacitance.

Figure 12. Break-Before-Make Interval Timing

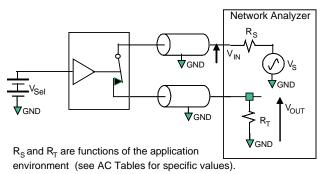
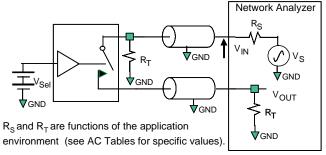
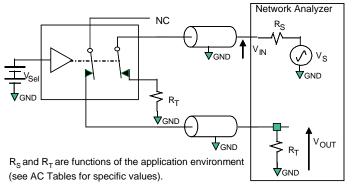


Figure 13. Bandwidth



Off isolation = 20 Log (V_{OUT} / V_{IN})

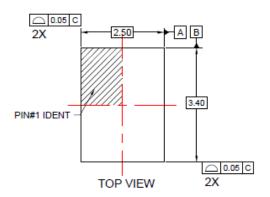
Figure 14. Channel Off Isolation

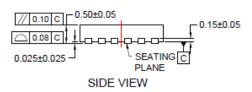


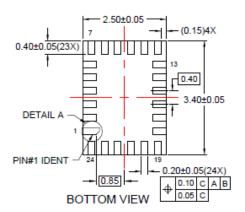
Crosstalk = 20 Log (V_{OUT} / V_{IN})

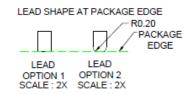
Figure 15. Non-Adjacent Channel-to-Channel Crosstalk

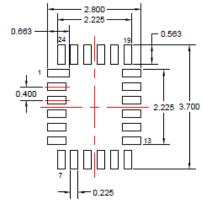
Physical Dimensions











RECOMMENDED LAND PATTERN

NOTES:

- PACKAGE DOES NOT FULLY CONFORM TO JEDEC STANDARD.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-UMLP24Arev3.

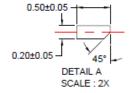


Figure 16. 24-Lead UMLP Package

Product-Specific Dimensions

Description	Nominal Values (mm)
Overall Height	0.500
PKG Standoff	0.026
Lead Thickness	0.152
Lead Width (24x)	0.200

Description	Nominal Values (mm)							
Lead Length (23x)	0.4							
Lead Length, Pin 1 (1x)	0.5							
Lead Pitch	0.4							
Body Length (X)	3.4							
Body Width (Y)	2.5							

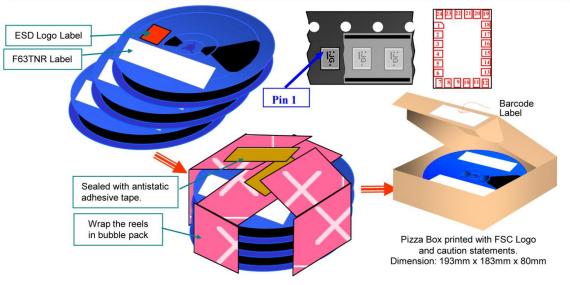
2.5x3.4 UMLP24L Packing - Embossed Tape FSA642UMX

Packing Description:

UMLP 24 pins products are classified under Moisture Sensitive Level 1.

The carrier tape is made from dissipative polystyrene or polycarbonate resin. The cover tape is a multilayer film primarily composed of polyester film, adhesive layer, heat activated sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5000 units per 178 mm diameter reel. Up to three reels are packed in each intermediate box. The reels is made of polystyrene plastic (anti-static coated or intrinsic).

These full reels are individually barcode labeled and placed inside a pizza box made of recyclable corrugated brown paper with a Fairchild logo printing. The reel is packed single reel in the pizza box. And these pizza boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



ESD Logo Label sample



Sample of F63TNR Label

SPEC:

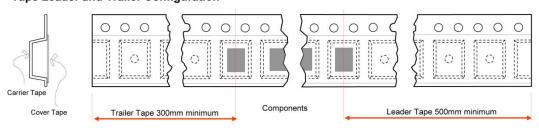
2nd Level Interconnect 1. Category G3

QTY: 5000

Maximum safe temperature 260 deg C
 MSL 1

(F63TNR)6.0

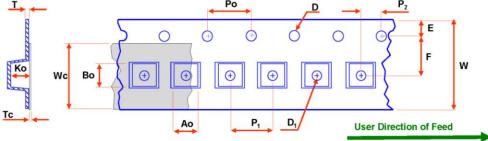
Tape Leader and Trailer Configuration



Rev 1 170810

Figure 17. Tape and Reel Packing Specification, page 1

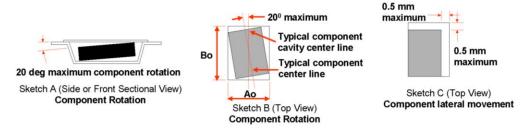
UMLP Embossed Tape Dimension

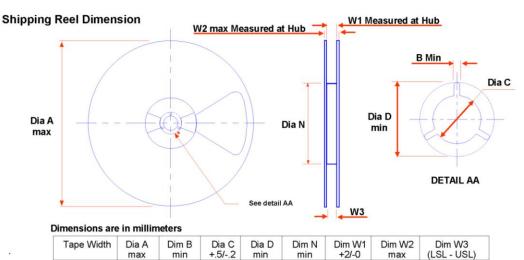


Dimensions are in millimeters

Package	Ao +/-0.05	Bo +/-0.05	D +/-0.10	D ₁ +/-0.05	E +/-0.1	F +/-0.05	Ko +/-0.05				T TYP	Tc +/-0.005	W +/-0.3	Wc TYP
UMLP24A	2.70	3.60	1.50	0.6	1.75	3.5	0.70	4	4	2.0	0.254	0.06	8	5.5

Notes: Ao, Bo, and Ko dimensions are determined with respect to the EIA /Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).





20.2

178

1.5

13

8

Figure 18. Tape and Reel Packing Specification, page 2

55

8.4

14.4

7.9~10.9

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